

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
30V	24m Ω @ $V_{GS} = 10V$	14.4A
	39m Ω @ $V_{GS} = 4.5V$	11.6A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

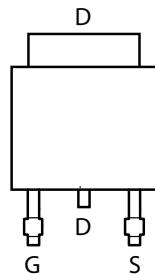
- Low on-resistance
- Fast switching speed
- Low gate drive
- "Green" component and RoHS compliant (Note 1)

Mechanical Data

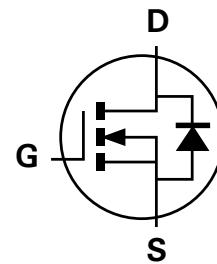
- Case: TO-252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Below
- Ordering Information: See Below
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3024LK3-13	N3024L	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



DII = Manufacturer's Marking
N3024L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-52)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source voltage		V_{DSS}	30	V
Gate-Source voltage		V_{GS}	± 20	V
Continuous Drain current	$V_{GS} = 10\text{V}$	I_D	14.4	A
			12.0	
			9.78	
Pulsed Drain current	$V_{GS} = 10\text{V}$	I_{DM}	46.5	A
Continuous Source current (Body diode)	(Note 3)	I_S	12	A
Pulsed Source current (Body diode)	(Note 4)	I_{SM}	46.5	A

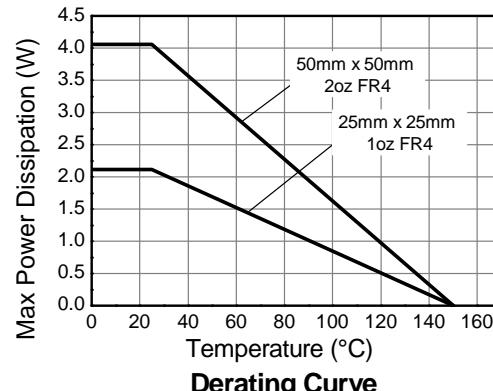
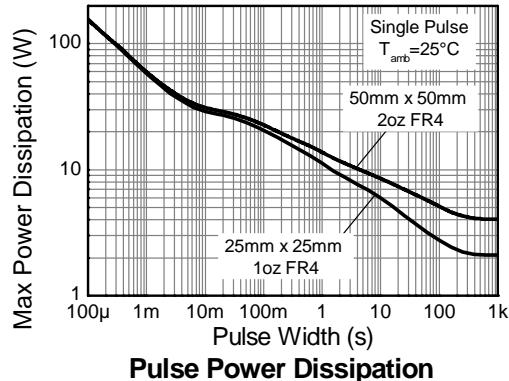
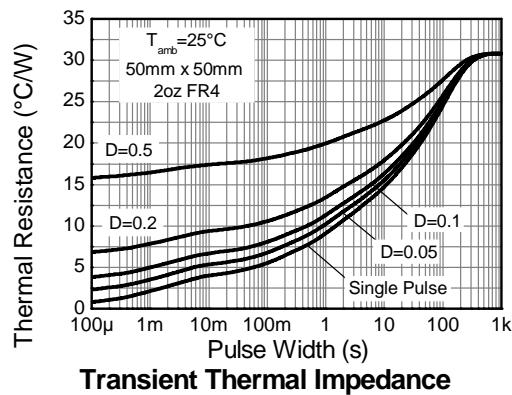
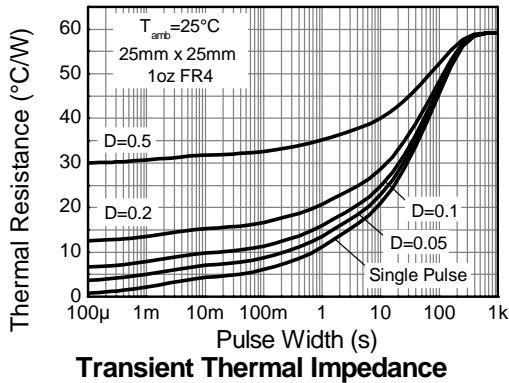
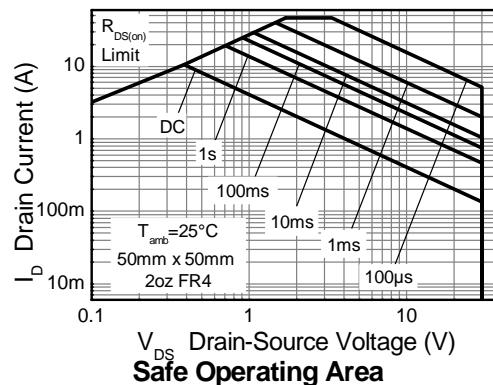
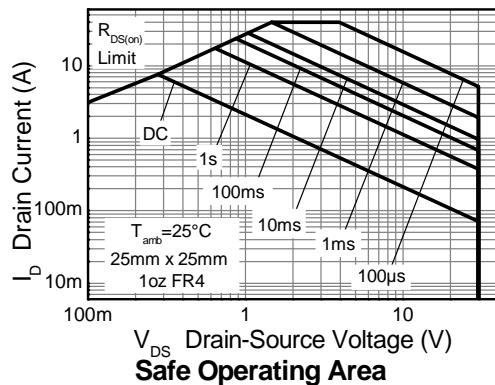
Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 2)	P_D	4.1	W mW/°C
	(Note 3)		32.5	
	(Note 5)		8.9	
Linear derating factor	(Note 2)	$R_{\theta JA}$	71.4	°C/W
	(Note 3)		2.17	
	(Note 5)		17.4	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	30.8	°C/W
	(Note 3)		14.0	
	(Note 5)		57.6	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	2.24	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:

2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note 2, except the device is measured at $t \leq 10$ sec.
4. Same as note 2, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics



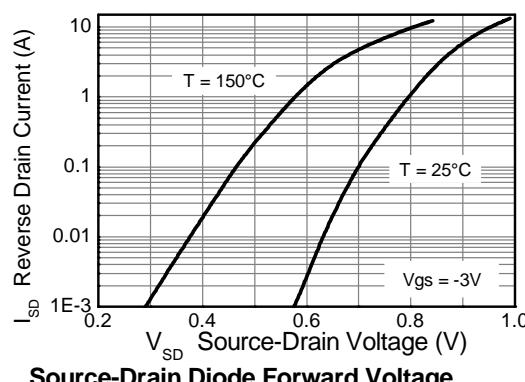
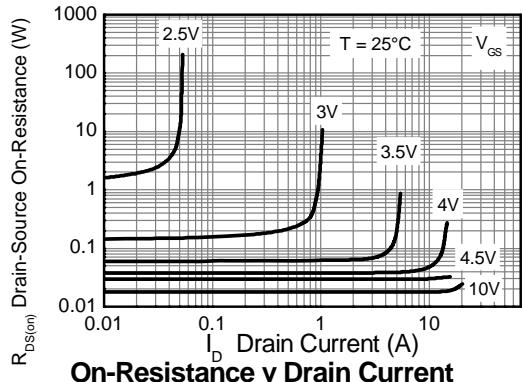
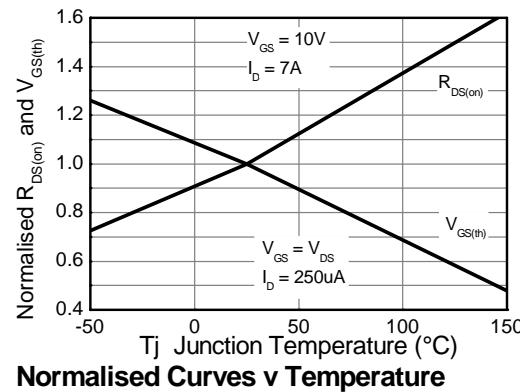
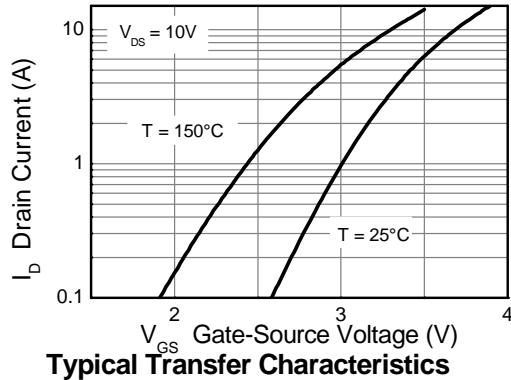
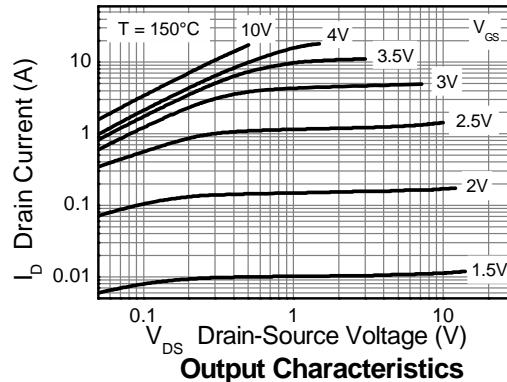
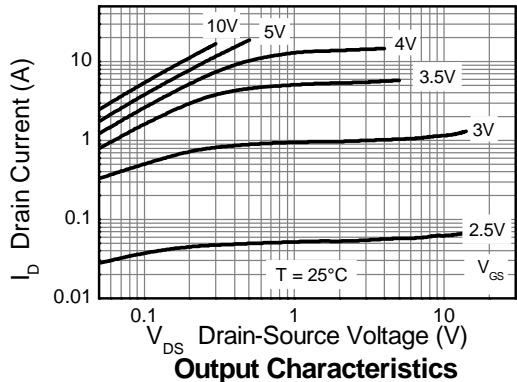
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{th})}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(\text{ON})}$	—	—	0.024	Ω	$V_{GS} = 10\text{V}$, $I_D = 7.0\text{A}$
				0.039		$V_{GS} = 4.5\text{V}$, $I_D = 6.0\text{A}$
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	16.5	—	S	$V_{DS} = 15\text{V}$, $I_D = 7.0\text{A}$
Diode Forward Voltage (Note 7)	V_{SD}	—	0.82	1.2	V	$I_S = 1.7\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery time (Note 8)	t_{rr}	—	12	—	ns	$I_S = 2.2\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 8)	Q_{rr}	—	4.8	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	608	—	pF	$V_{DS} = 15\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	71	—	pF	
Total Gate Charge	Q_g	—	12.9	—	nC	$V_{DS} = 15\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 7\text{A}$
Gate-Source Charge	Q_{gs}	—	2.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.5	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(\text{on})}$	—	2.9	—	ns	
Turn-On Rise Time (Note 9)	t_r	—	3.3	—	ns	$V_{DD} = 15\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 1\text{A}$, $R_G \geq 6.0\Omega$
Turn-Off Delay Time (Note 9)	$t_{D(\text{off})}$	—	16	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	8	—	ns	

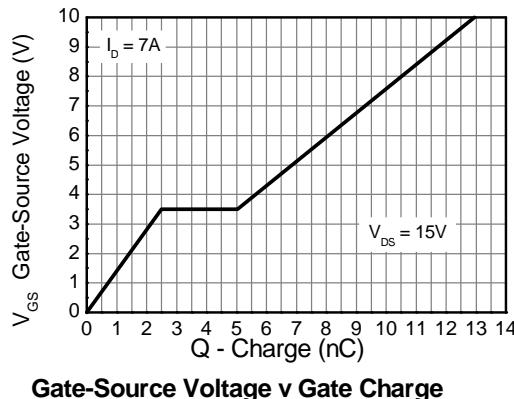
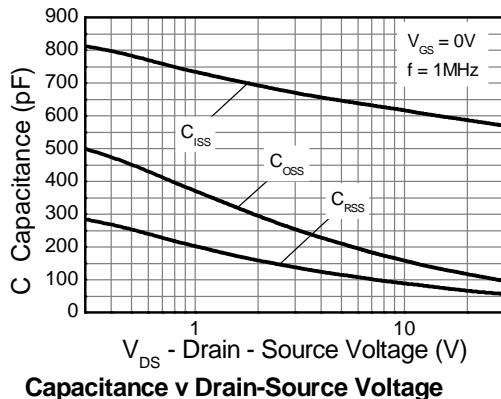
Notes:

- 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$
- 8. For design aid only, not subject to production testing.
- 9. Switching characteristics are independent of operating junction temperatures.

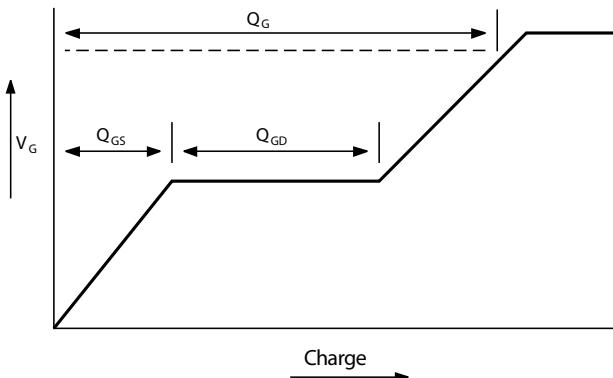
Typical Characteristics



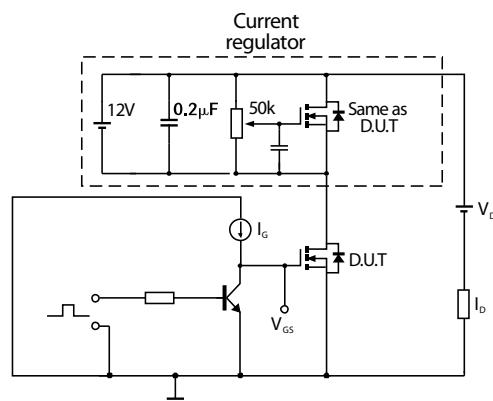
Typical Characteristics - continued



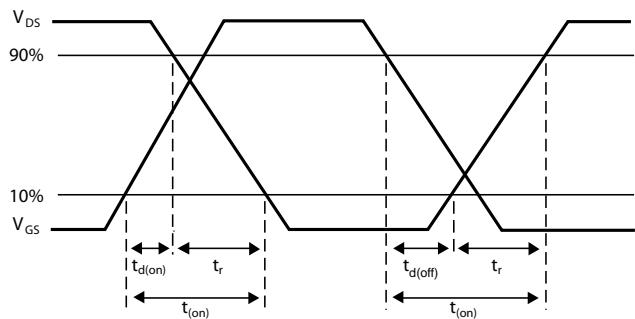
Test Circuits



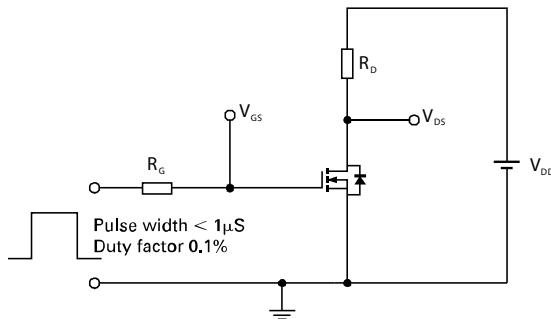
Basic gate charge waveform



Gate charge test circuit

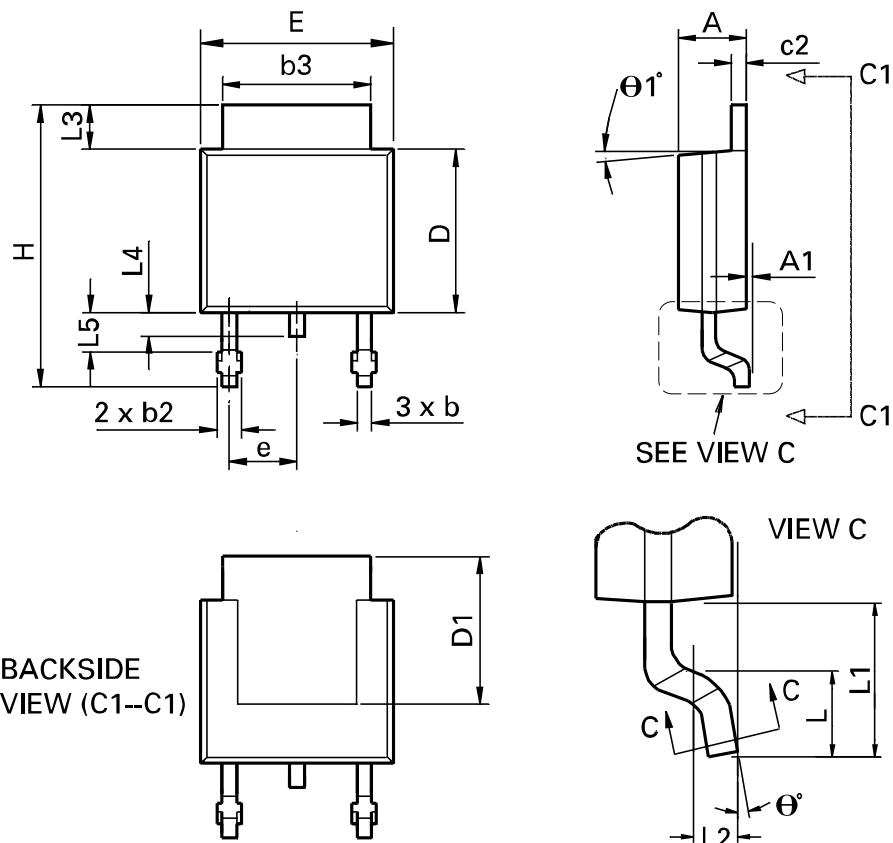


Switching time waveforms



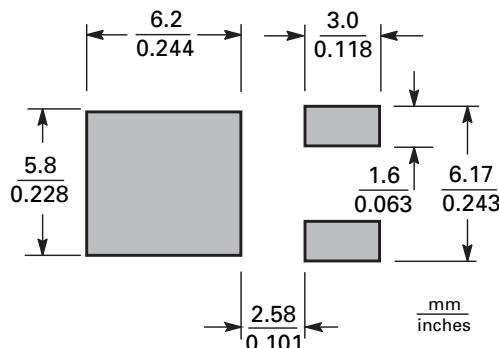
Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	$\Theta 1^\circ$	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	Θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Suggested Pad Layout



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